

Voltage Variable Absorptive Attenuator
35 dB, DC - 2.0 GHz

AT-635
V6

Features

- 35 dB Voltage Variable Attenuation at 1 GHz
- Single Voltage Control: 0 to -4 Volts
- Low DC Power Consumption
- Nanosecond Switching Speed
- Temperature Range: -40°C to +85°C
- SOIC-14 Plastic Package
- Tape and Reel Packaging Available

Description

M/A-COM's AT-635 is a GaAs MMIC voltage variable absorptive attenuator in a low cost SOIC 14-lead surface mount plastic package. The AT-635 is ideally suited for use where attenuation fine tuning, fast switching and very low power consumption are required.

Typical applications include radio, cellular, GPS equipment and other automatic gain/level control circuits.

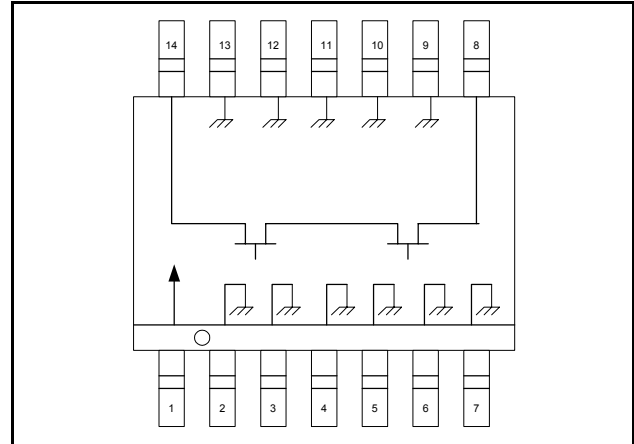
The AT-635 is fabricated with a monolithic GaAs MMIC using a mature 1-micron process. The process features full chip passivation for increased performance and reliability.

Ordering Information

| Part Number | Package |
|-------------|------------------------------|
| AT-635 | SOIC 14-Lead Plastic Package |
| AT-635TR | Tape and Reel |

Note: Reference Application Note M513 for reel size information.

Functional Schematic



Pin Configuration

| Pin No. | Function | Pin No. | Function |
|---------|----------------|---------|----------|
| 1 | V _C | 8 | RF2 |
| 2 | Ground | 9 | Ground |
| 3 | Ground | 10 | Ground |
| 4 | Ground | 11 | Ground |
| 5 | Ground | 12 | Ground |
| 6 | Ground | 13 | Ground |
| 7 | Ground | 14 | RF1 |

Absolute Maximum Ratings^{1,2}

| Parameter | Absolute Maximum |
|-----------------------|--------------------------------|
| Input Power | +21 dBm |
| Control Voltage | -8.5 V ≤ V _C ≤ +5 V |
| Operating Temperature | -40°C to +85°C |
| Storing Temperature | -65°C to +150°C |

1. Exceeding any one or combination of these limits may cause permanent damage to this device.
2. M/A-COM does not recommend sustained operation near these survivability limits.

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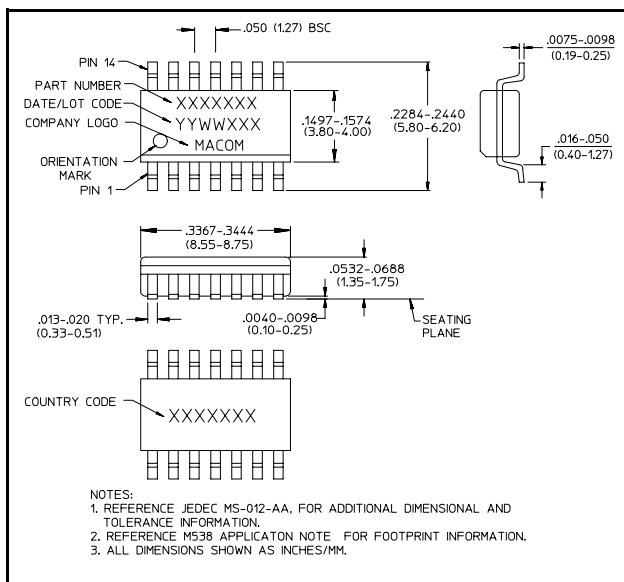
Electrical Specifications: $T_A = 25^\circ\text{C}$, $Z_0 = 50 \Omega$

| Parameter | Test Conditions ³ | Units | Min. | Typ. | Max. |
|----------------------------|--|-------|------|-----------------|-----------|
| Insertion Loss | DC - 0.5 GHz | dB | — | 6.7 | 7.0 |
| | 0.5 - 1.0 GHz | dB | — | 7.2 | 7.4 |
| | 1.0 - 2.0 GHz | dB | — | 7.5 | 7.8 |
| Flatness (Peak to Peak) | 10 dB Attenuation – DC - 2.0 GHz | dB | — | ± 1.0 | ± 1.3 |
| | 20 dB Attenuation – DC - 2.0 GHz | dB | — | ± 1.2 | ± 1.5 |
| | 30 dB Attenuation – DC - 2.0 GHz | dB | — | ± 1.2 | ± 1.5 |
| VSWR | | Ratio | — | 2.0:1 | — |
| Trise, Tfall | 10% to 90% RF, 90% to 10% RF | nS | — | 2 | — |
| Ton, Toff | 50% Control to 90% RF, 50% Control to 10% RF | nS | — | 4 | — |
| Transients | In Band | mV | — | 30 | — |
| Power Handling | Linear Operation | dBm | — | — | 13 |
| | Absolute maximum Input Power | dBm | — | — | 21 |
| IP ₂ | 0.05 GHz | dBm | — | 34 | — |
| | 0.5 - 2.0 GHz Measured Relative to Input Power (For two-tone Input Power Up to +5 dBm) | dBm | — | 47 | — |
| IP ₃ | 0.05 GHz | dBm | 18 | 31 ⁴ | — |
| | 0.5 - 2.0 GHz Measured Relative to Input Power (For two-tone Input Power Up to +5 dBm) | dBm | 18.5 | 36 ⁴ | — |

3. Control voltage: 0 to -4 volts @ 20 μA typical.

4. For levels above 6 dB attenuation. For levels below 6 dB, the minimum specification numbers apply.

SOIC-14



Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

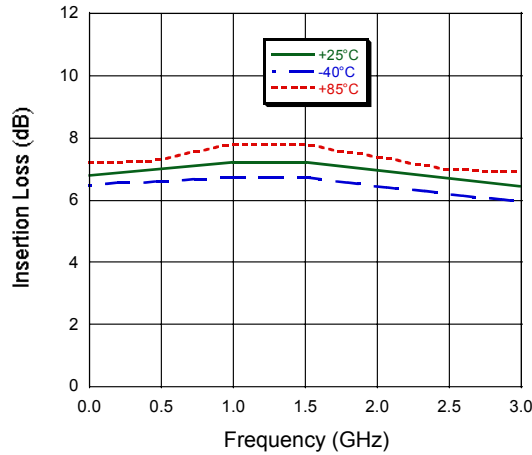
Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

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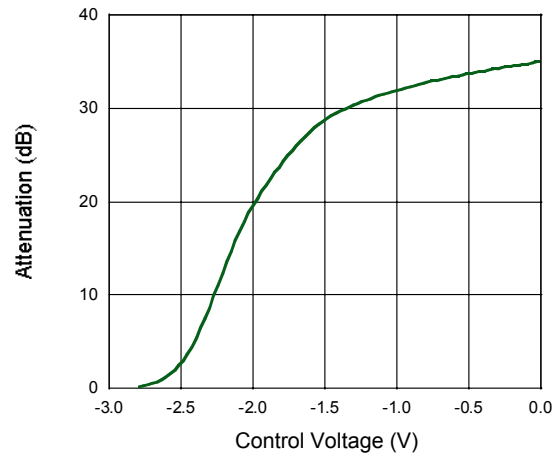
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Typical Performance Curves

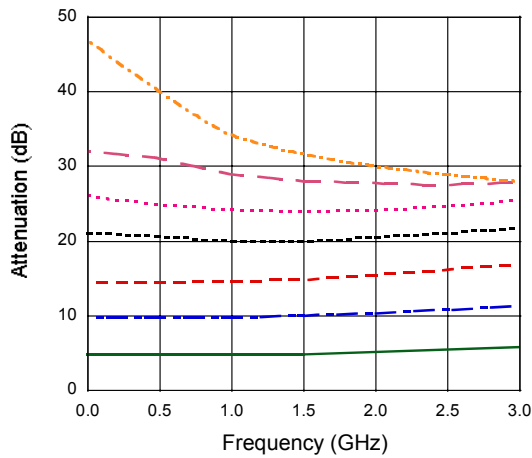
Insertion Loss vs. Frequency



Attenuation vs. Control Voltage, F = 1 GHz



Attenuation vs. Frequency



VSWR vs. Frequency

